

# Bias Resistor Transistor

## PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

**LDTA144WWT1G**

● **Applications**

Inverter, Interface, Driver

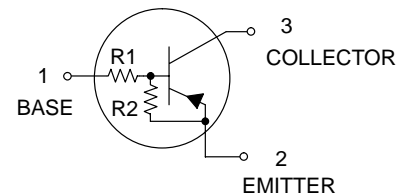
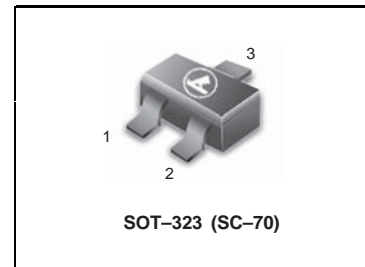
● **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

● **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V <sub>cc</sub>	-50	V
Input voltage	V <sub>i</sub>	-40 to +10	V
Output current	I <sub>o</sub>	-30	mA
	I <sub>c(Max.)</sub>	-100	
Power dissipation	P <sub>d</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



**DEVICE MARKING AND RESISTOR VALUES**

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA144WWT1G	6P	47	22	3000/Tape & Reel
LDTA144WWT3G	6P	47	22	8000/Tape & Reel

● **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V <sub>i(off)</sub>	-	-	-0.8	V	V <sub>cc</sub> = -5V, I <sub>o</sub> = -100μA
	V <sub>i(on)</sub>	-4	-	-		V <sub>o</sub> = -0.3V, I <sub>o</sub> = -2mA
Output voltage	V <sub>O(on)</sub>	-	-0.1	-0.3	V	I <sub>o</sub> = -10mA, I <sub>i</sub> = -0.5mA
Input current	I <sub>i</sub>	-	-	-0.16	mA	V <sub>i</sub> = -5V
Output current	I <sub>o(off)</sub>	-	-	-0.5	μA	V <sub>cc</sub> = -50V, V <sub>i</sub> =0V
DC current gain	G <sub>i</sub>	56	-	-	-	I <sub>o</sub> = -5mA, V <sub>o</sub> = -5V
Input resistance	R <sub>1</sub>	32.9	47	61.1	kΩ	-
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.37	0.47	0.57	-	-
Transition frequency	f <sub>T</sub>	-	250	-	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f=100MHz *

\* Transition frequency of the device.

**LDTA144WWT1G**

● **Electrical characteristic curves**

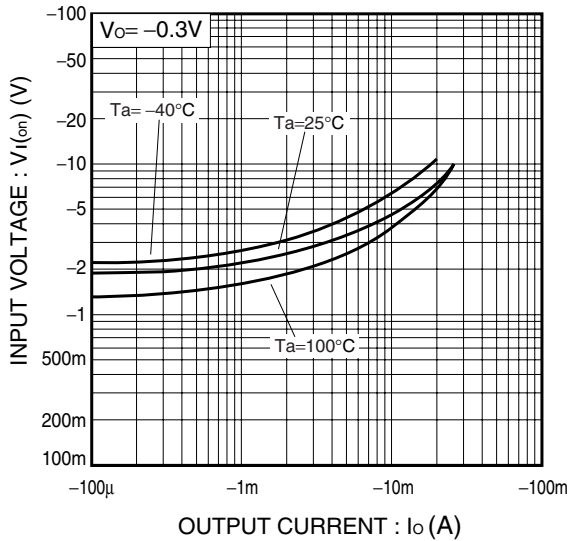


Fig.1 Input voltage vs. Output current

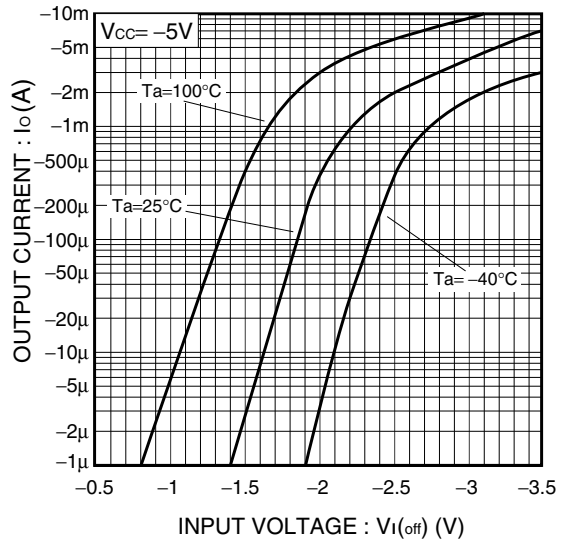


Fig.2 Output current vs. Input voltage

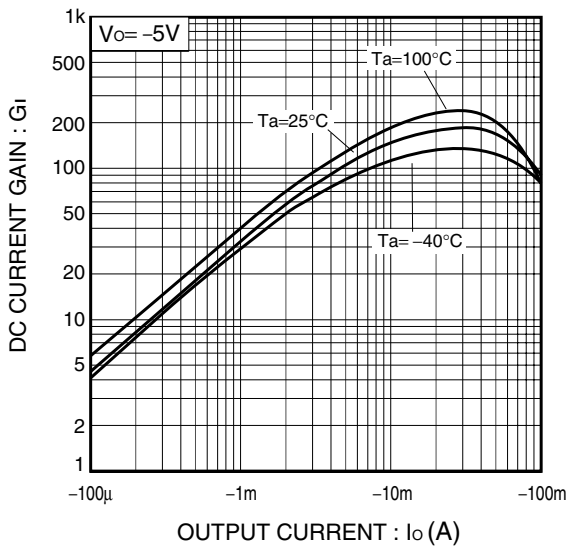


Fig.3 DC current gain vs. Output current

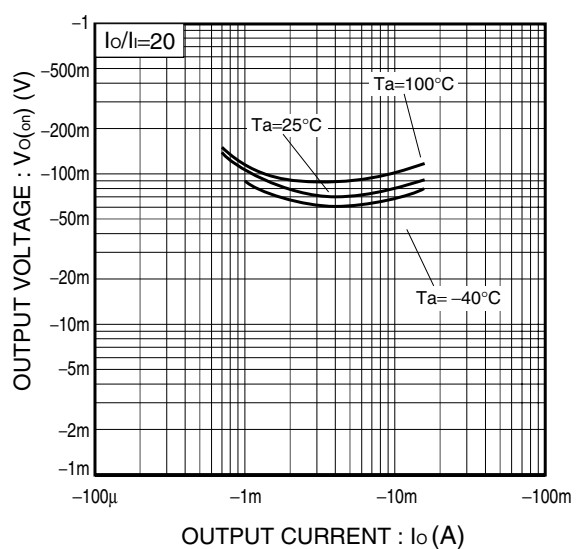
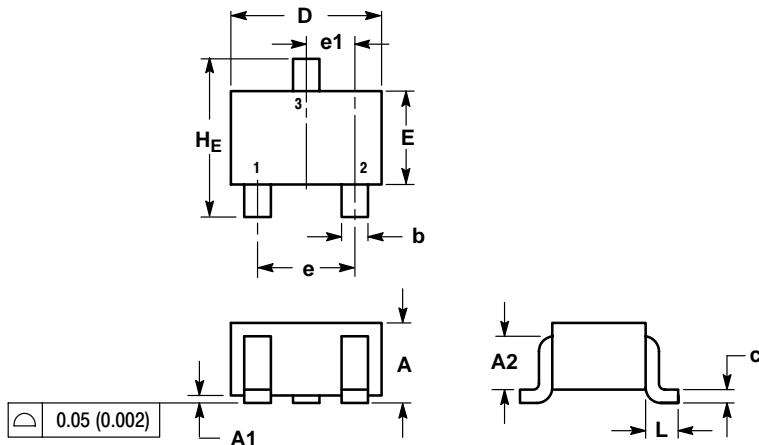


Fig.4 Output voltage vs. Output current

**LDTA144WWT1G**

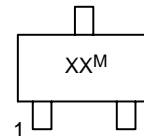
**SC-70 (SOT-323)**



NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

**GENERIC MARKING DIAGRAM**



XX = Specific Device Code  
 M = Date Code  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***

